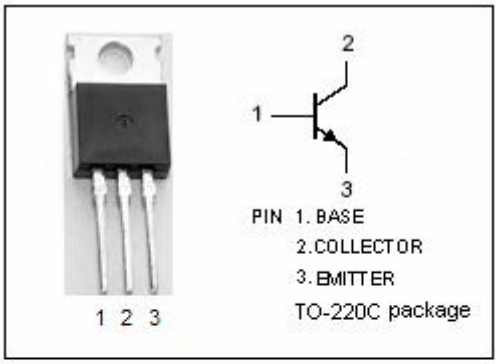
isc Silicon NPN Power Transistor 2SC2336

DESCRIPTION

- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 180V(Min)
- Wide Area of Safe Operation
- Complement to Type 2SA1006
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

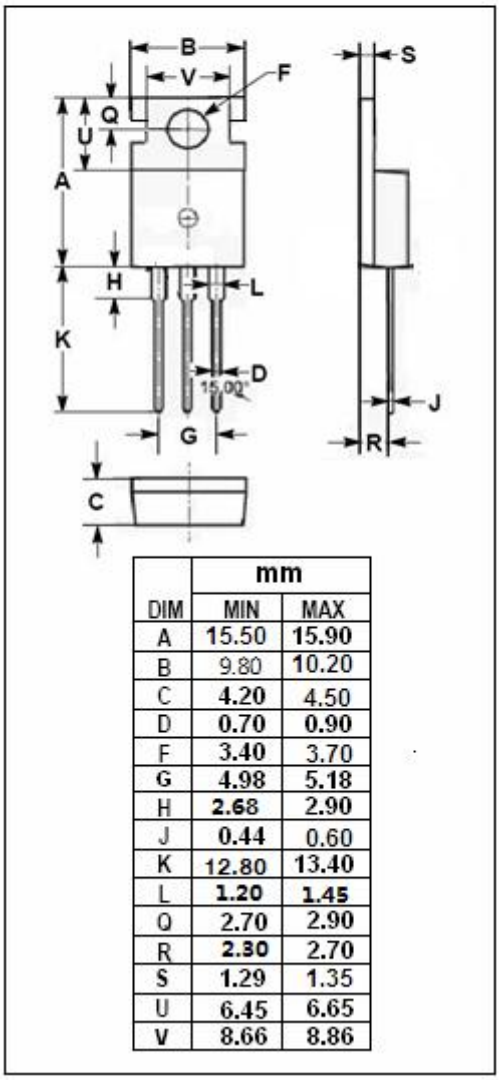


APPLICATIONS

- Adudio frequency power amplifier
- High frequency power amplifier

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	180	V
V_{CEO}	Collector-Emitter Voltage	180	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current-Continuous	1.5	A
I_{CM}	Collector Current-Peak	3.0	A
P_C	Collector Power Dissipation@ T_a=25℃	1.5	W
	Collector Power Dissipation@T_C=25℃	25	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$★	Collector-Emitter Saturation Voltage	I_C= 500mA; I_B= 50mA			1.0	V
$V_{BE(sat)}$★	Base-Emitter Saturation Voltage	I_C= 500mA; I_B= 50mA			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 150V; I_E= 0			1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 3.0V; I_C=0			1.0	μA
h_{FE-1}★	DC Current Cain	I_C= 5mA ; V_{CE}= 5V	30			
h_{FE-2}★	DC Current Cain	I_C= 150mA ; V_{CE}= 5V	60		320	
f_T	Current-Gain—Bandwidth Product	I_C= 100mA ; V_{CE}= 10V		95		MHz
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= 10V;f_{test}= 1.0MHz		30		pF

★Pulse Test/PW≦350us,duty≦2%

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	100-200	160-320